

ABSTRACT OF THE DISCLOSURE

An improved semiconductor laser device is provided which has a small distance between laser light emitting spots. Such laser device comprises i) a first light emitting element including a laser oscillation section provided with a ridge waveguide and formed by forming a group-III nitride semiconductor film on a substrate, an insulating layer and an ohmic electrode layer, ii) a second light emitting element including a laser oscillation section provided with a waveguide and formed by forming III-V compound semiconductor film, an insulating layer and an ohmic electrode layer. By virtue of the adhesivemetal layer interposed between the two ohmic electrode layers, the two laser oscillation sections are combined together, thereby forming the improved semiconductor laser device which has a small distance between laser light emitting spots of the two laser oscillation sections.